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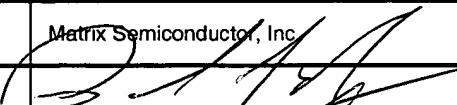
Total Number of Pages in This Submission

Application Number	10/815,312
Filing Date	April 1, 2004
First Named Inventor	Yung-Tin Chen
Art Unit	1756
Examiner Name	Stephen D Rosasco
Attorney Docket Number	MA-117

ENCLOSURES (Check all that apply)

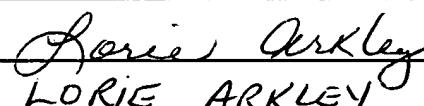
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Firm Name	Matrix Semiconductor, Inc.		
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Printed name	Pamela J. Squyres		
Date	6/23/05	Reg. No.	52246

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Yung-Tin Chen	Group Art Unit: 1756
Application No.: 10/815,312	Examiner: Stephen D. Rosasco
Filed: April 1, 2004	
Title: Photomask Features with Chromeless Nonprinting Phase Shifting Window	
Attorney Docket No.: MA-117	

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

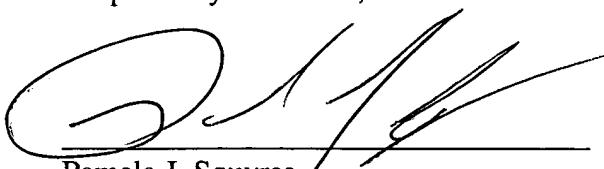
Dear Sir or Madam,

Pursuant to the obligation under 37 CFR § 1.56 and in conformance with 37 CFR §§ 1.97-1.99, Applicant hereby submits documents A1-A37 as listed on the attached form PTO-1449 for consideration by the Examiner. Copies of reference documents A9–A37 are enclosed herewith. Applicant requests that the Examiner review the entire disclosure of these documents and make them of record.

The filing of this Information Disclosure Statement does not constitute an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR §1.56(b). Further Applicant reserves the right to contest that any of the information submitted herewith is prior art against the present application.

Dated: 6/23/05

Respectfully submitted,



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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		<i>Complete if Known</i> Application Number 10/815,312 Filing Date April 1, 2004 First Named Inventor Chen, Yung-Tin Group Art Unit 1756 Examiner Name Rosasco, Stephen	
 Sheet 1 of 3		Attorney Docket No: MA-117	

US PATENT DOCUMENTS

Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	A1	5,240796	08/31/1993	Lee et al.			
	A2	6,057063	05/02/2000	Liebmann et al.			
	A3	6,482555	11/19/2002	Chen et al.			
	A4	6,523165	02/18/2003	Liu et al.			
	A5	6,541165	04/01/2003	Pierrat			
	A6	6,551750	04/22/2003	Pierrat			
	A7	6,569583	05/27/2003	Cho et al.			
	A8	20030022074	01/30/2003	Nolscher			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	A9	BERNARD, DOUGLAS.A. , et al. , "Clear Field Dual Alternating Phase Shift Mask Lithography", <u>Optical Microlithography XV</u> , SPIE Vol. 4691, (2002),999-1008	
	A10	BURKHARDT, M.,et al. , "Through Pitch Correction of Scattering Effects in 193 nm Alternating Phase Shift Masks", <u>Optical Microlithography XV</u> Vol. 4691, No. I, SPIE, (2002),348-358	
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		First Named Inventor	Chen, Yung-Tin
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		Examiner Name	Rosasco, Stephen
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		for Alternating PSM-Control of Forbidden Pitches", <u>Optical Microlithography XV</u> , Vol. 4691, No.I, SPIE, (2002),240-246	
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A22		MAURER, WILHELM.,et al. , "Proximity Effects of Alternating Phase Shift Masks", <u>19th Annual Symposium on Photomask Technology</u> , Vol. 3873, No. I, SPIE, (9/1999),344-349	
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Sheet 3 of 3		Attorney Docket No: MA-117	

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	A31	TAN, SIA.K. , "Optimization of Alternating PSM Mask Process for 65 nm Poly Gate Patterning Using 193 nm Lithography", <u>Optical Microlithography XVI</u> , SPIE Vol. 5040, (2003),1125-1136	
	A32	THIELE, JORG.,et al. , "Introduction of full level alternating phase shift mask technology into IC manufacturing", <u>Optical Microlithography XV</u> , Vol. 4691, No.1, SPIE, (2002),89-97	
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	A34	WESTERMAN, R.,et al. , "Plasma Etching of Quartz for the Fabrication of Alternating Aperture Phase Shift Photomasks: Etch Rate Uniformity Study", <u>20th Annual BACUS Symposium on Photomask Technology</u> , Vol. 4186, SPIE, (2001),316-324	
	A35	WU, CLIVE., "Alternating PSM Design and Its Implications to the Design-to-Manufacturing Flow", <u>?</u> , Numerical Technologies, Inc. 70 W. Plumeria Dr., San Jose, CA 95134, 7 pgs	
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